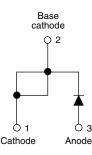


Vishay Semiconductors

### HEXFRED<sup>®</sup>, Ultrafast Soft Recovery Diode, 6 A





PRODUCT SUMMARY							
Package	TO-220AC						
I <sub>F(AV)</sub>	6 A						
V <sub>R</sub>	1200 V						
V <sub>F</sub> at I <sub>F</sub>	3.0 V						
t <sub>rr</sub> typ.	26 ns						
T <sub>J</sub> max.	150 °C						
Diode variation	Single die						

#### FEATURES

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Designed and qualified according to JEDEC®-JESD47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

#### BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

#### DESCRIPTION

VS-HFA06TB120... is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06TB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (IRBM) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06TB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V <sub>R</sub>		1200	V					
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	6						
Single pulse forward current	I <sub>FSM</sub>		80	А					
Maximum repetitive forward current	I <sub>FRM</sub>		24						
Maximum namer dissinction	P	T <sub>C</sub> = 25 °C	62.5	W					
Maximum power dissipation	PD	T <sub>C</sub> = 100 °C	25	vv					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55 to +150	°C					

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Document Number: 94038

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<b>ELECTRIACL SPECIFICATIONS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	1200	-	-					
Maximum forward voltage		I <sub>F</sub> = 6.0 A	-	2.7	3.0	V				
	V <sub>FM</sub>	I <sub>F</sub> = 12 A	-	3.5	3.9					
		I <sub>F</sub> = 6.0 A, T <sub>J</sub> = 125 °C	-	2.4	2.8					
Maximum reverse		$V_R = V_R$ rated	-	0.26	5.0					
leakage current	IRM	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	110	500	μA				
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	9.0	14	pF				
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time	t <sub>rr</sub>	$I_F = 1.0 \text{ A},  dI_F/dt = 200$	A/μs, V <sub>R</sub> = 30 V	-	26	-	ns			
	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	53	80				
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	87	130				
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.4	8.0	- A nC - Α/μs			
	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 6.0 A dI <sub>F</sub> /dt = 200 A/µs	-	5.0	9.0				
	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	116	320				
Reverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	233	585				
Peak rate of recovery current during $\mathbf{t}_{b}$	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	180	-				
	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	100	-				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C				
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	2.0					
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W				
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-					
Weight			-	2.0	-	g				
weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Marking device		Case style TO-220AC	HFA06TB120							

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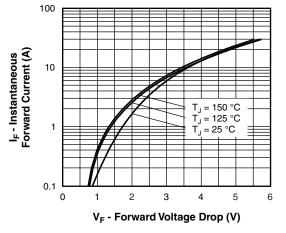
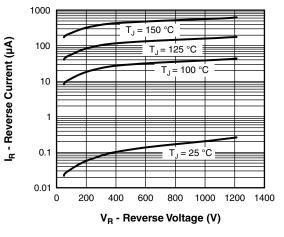
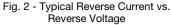


Fig. 1 - Typical Forward Voltage Drop Characteristics





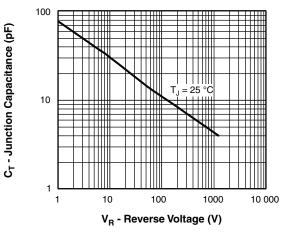
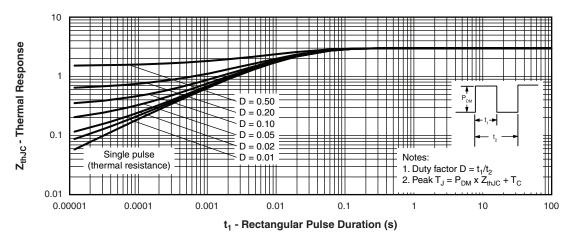


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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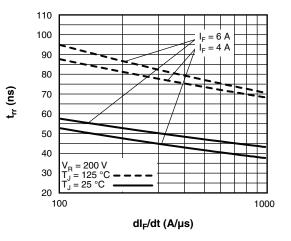


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

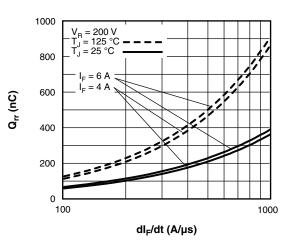


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

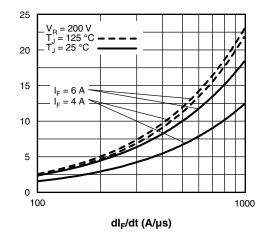


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

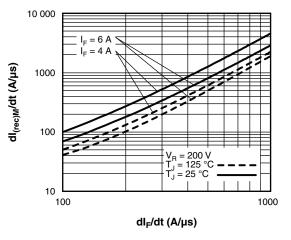


Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt

I<sub>rr</sub> (A)



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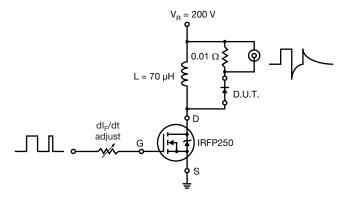


Fig. 9 - Reverse Recovery Parameter Test Circuit

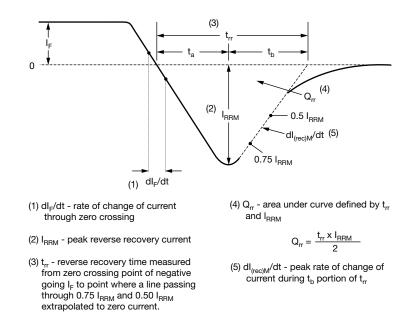
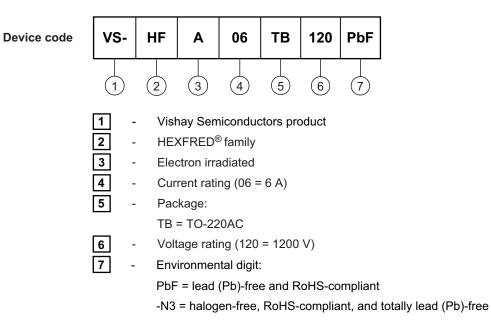


Fig. 10 - Reverse Recovery Waveform and Definitions



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#### **ORDERING INFORMATION TABLE**



ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-HFA06TB120PbF	50	1000	Antistatic plastic tube						
VS-HFA06TB120-N3	50	1000	Antistatic plastic tube						

LINKS TO RELATED DOCUMENTS							
Dimensions		www.vishay.com/doc?95221					
Part marking information	TO-220ACPbF	www.vishay.com/doc?95224					
	TO-220AC-N3	www.vishay.com/doc?95068					



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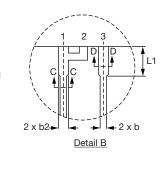
**TO-220AC** 

plane

#### **DIMENSIONS** in millimeters and inches









**Diodes** 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

SYMBOL	MILLIN	IETERS	INC	HES	NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES	
STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES		STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183			E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055			E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115			е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040			e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4		H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068			L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4		L1	3.32	3.82	0.131	0.150	2
с	0.36	0.61	0.014	0.024			L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4		L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3		ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355			Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6		θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6							

Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

- <sup>(2)</sup> Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- <sup>(4)</sup> Dimension b1, b3 and c1 apply to base metal only
- <sup>(5)</sup> Controlling dimension: inches
- <sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1
- <sup>(7)</sup> Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- <sup>(8)</sup> Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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